What is Claimed is:

1. A semiconductor device comprising:
a semiconductor substrate;
wirings located on the semiconductor substrate; and
a passivation film, located on the wirings, including a first insulating film which contains an impurity,
wherein the first insulating film is formed from silicon oxide film materials containing over 1% carbon.

2. The semiconductor device according to claim 1, wherein the impurity is selected from the group consisting of argon, nitrogen and phosphorus.

3. The semiconductor device according to claim 1, wherein the impurity is boron.

4. A semiconductor device comprising:
a semiconductor substrate;
wirings located on the semiconductor substrate; and
a passivation film, located on the wirings, including a first insulating film which contains an impurity,
wherein the first insulating film includes an inorganic SOG(Spin-on-Glass).

5. The semiconductor device according to claim 4, wherein the impurity is boron.

6. A semiconductor device comprising:
a semiconductor substrate;
wirings located on the semiconductor substrate; and
a passivation film located on the wirings, including a

first insulating film and a second insulating film, wherein the first insulating film contains an impurity and is formed from silicon oxide film materials containing over 1% carbon, and the second insulating film is located on at least one of an upper side and a lower side of the first insulating film.

7. The semiconductor device according to claim 6, wherein the second insulating film has a hygroscopicity lower than the first insulating film.

8. The semiconductor device according to claim 6, wherein the second insulating film is selected the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

9. The semiconductor device according to claim 6, wherein the impurity is selected from the group consisting of argon, nitrogen and phosphorus.

10. The semiconductor device according to claim 6, wherein the impurity is boron.

11. A semiconductor device comprising:

a semiconductor substrate;

wirings located on the semiconductor substrate; and

a passivation film located on the wirings, including a first insulating film and a second insulating film, wherein the first insulating film includes an inorganic SOG(Spin-on-Glass) film containing an impurity, and the second insulating film is located on at least one of an upper side and a lower side of the first insulating film.

12. The semiconductor device according to claim 11, wherein the second insulating film has a hygroscopicity lower than the first insulating film.

13. The semiconductor device according to claim 11, wherein the second insulating film is selected the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

14. The semiconductor device according to claim 11, wherein the impurity is selected from the group consisting of argon, nitrogen and phosphorus.

15. The semiconductor device according to claim 11, wherein the impurity is boron.

16. A method of fabricating a semiconductor device, comprising the steps of:

forming wirings on a semiconductor substrate;

forming a passivation film including a first insulating film on the wirings; and

introducing an impurity into the first insulating film.

17. The method according to claim 16, further comprising the step of forming a second insulating film included in the passivation film on at least one of an upper side and a lower side of the first insulating film.

18. The method according to claim 17, wherein the second insulating film has a hygroscopicity lower than the first insulating film.

19. The method according to claim 16, wherein the second insulating film is selected the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

20. The method according to claim 16, wherein the step of forming the passivation film includes the step of forming a first insulating film on the wirings using silicon oxide film materials containing over 1% carbon.

21. The method according to claim 16, wherein the step of forming the passivation film includes the step of forming a first insulating film on the wirings using an inorganic SOG(Spin-on-Glass).

22. The method according to claim 16, wherein the impurity is introduced by implantation.

23. The method according to claim 16, wherein the impurity is selected from the group consisting of argon, nitrogen and phosphorus.

24. The method according to claim 16, wherein the impurity is boron.